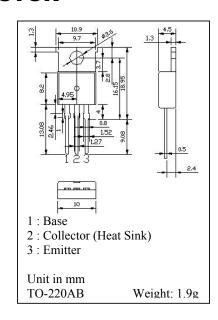


TRIPLE DIFFUSED SILICON NPN TRANSISTOR

... designed for low frequency power amplifier

MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	100	V
Collector Emitter Voltage	V _{CEO}	80	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current (DC)	I_C	4	Α
Collector Current (Peak)	I_C	8	Α
Collector power Dissipation	Pc	40	W
Junction Temperature	T_{J}	150	°C
Storage Temperature	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS

Symbol	Test Condition	Min.	Тур.	Max.	Unit
I_{CBO}	$V_{CB} = 80V$, $I_E = 0A$	ı	-	100	μΑ
V _{(BR)CEO}	$I_C = 50 \text{mA}, I_B = 0 \text{A}$	80	-	ı	V
h_{FE}	$V_{CE} = 4V$, $I_{C} = 1A$	60	-	200	-
	$V_{CE} = 4V$, $I_{C} = 0.1A$	35	-	-	-
V _{CE(sat)}	$I_C = 2A$, $I_B = 0.2A$	ı	-	1	V
V_{BE}	$V_{CE} = 4V$, $I_{C} = 1A$	-	-	1.5	V
f_T	$V_{CE} = 5V$, $I_{C} = 0.5A$	-	10	1	MHz
C_{ob}	$V_{CB} = 20V$, $I_E = 0A$, $f=1MHz$	-	40	-	Pf
	I_{CBO} $V_{(BR)CEO}$ h_{FE} $V_{CE(sat)}$ V_{BE} f_{T}	$\begin{split} & I_{CBO} & V_{CB} = 80 V, I_E = 0 A \\ & V_{(BR)CEO} & I_C = 50 mA, I_B = 0 A \\ & h_{FE} & V_{CE} = 4 V, I_C = 1 A \\ & V_{CE} = 4 V, I_C = 0.1 A \\ & V_{CE(sat)} & I_C = 2 A, I_B = 0.2 A \\ & V_{BE} & V_{CE} = 4 V, I_C = 1 A \\ & V_{CE} = 5 V, I_C = 0.5 A \end{split}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

HIGH POWER DISSIPATION MEDIUM SPEED

POWER
SWITCHING

Classification of hFE

Rank	В	С	
Range	60 to 120	100-200	



TO - 220AB

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